

Features

- Ultrafast body diode
- Rugged polysilicon gate cell structure
- Increased Unclamped Inductive Switching (UIS) capability
- Hermetically sealed, surface mount power package
- Low package inductance
- Very low thermal resistance
- Reverse polarity available upon request

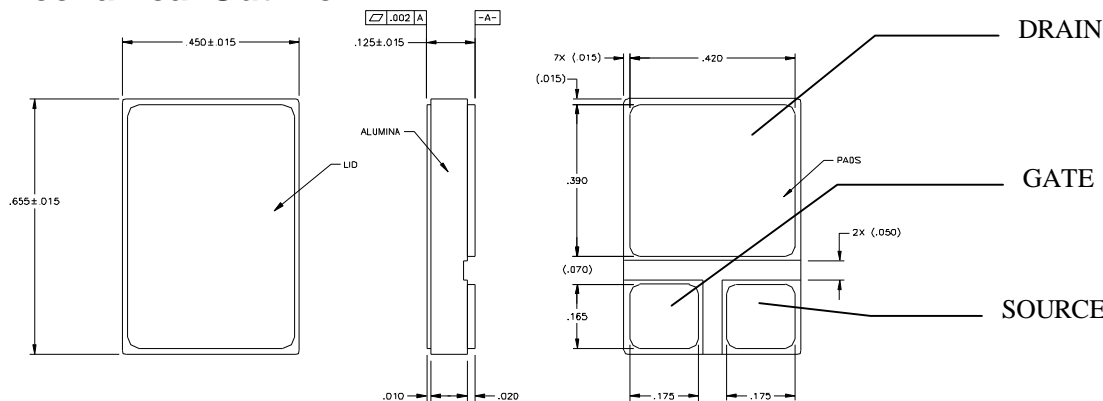
900 Volts
10 Amps
1.1 W

N-CHANNEL
ENHANCEMENT MODE
POWER MOSFET

Maximum Ratings @ 25°C (unless otherwise specified)

DESCRIPTION	SYMBOL	MAX.	UNIT
Drain-to-Source Breakdown Voltage (Gate Shorted to Source) @ $T_J \geq 25^\circ\text{C}$	BV_{DSS}	900	Volts
Drain-to-Gate Breakdown Voltage @ $T_J \geq 25^\circ\text{C}$, $R_{GS} = 1\text{ M}\Omega$	BV_{DGR}	900	Volts
Continuous Gate-to-Source Voltage	V_{GS}	+/-20	Volts
Transient Gate-to-Source Voltage	V_{GSM}	+/-30	Volts
Continuous Drain Current 100°C	I_{D25} I_{D100}	10 6	Amps
Peak Drain Current, pulse width limited by T_{Jmax}	I_{DM}	40	Amps
Repetitive Avalanche Current	I_{AR}	10	Amps
Repetitive Avalanche Energy	E_{AR}	30	mJ
Single Pulse Avalanche Energy	E_{AS}	tbd	mJ
Voltage Rate of Change of the Recovery Diode @ $I_S \leq I_{DM}$, $di/dt \leq 100\text{ A}/\mu\text{s}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$	dv/dt	5.0	V/ns
Power Dissipation	P_D	300	Watts
Junction Temperature Range	T_J	-55 to +150	°C
Storage Temperature Range	T_{stg}	-55 to +150	°C
Continuous Source Current (Body Diode)	I_S	10	Amps
Pulse Source Current (Body Diode)	I_{SM}	40	Amps
Thermal Resistance, Junction to Case	θ_{JC}	0.25	°C/W

Mechanical Outline



Electrical Parameters @ 25°C (unless otherwise specified)

DESCRIPTION	SYMBOL	CONDITIONS	MIN	TYP.	MAX	UNIT
Drain-to-Source Breakdown Voltage (Gate Shorted to Source)	BV_{DSS}	$V_{GS} = 0\text{ V}, I_D = 3\text{ mA}$	900			V
Temperature Coefficient of the Drain-to-Source Breakdown Voltage	$\Delta BV_{DSS}/\Delta T_J$			0.6		V/°C
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 4\text{ mA}$	2.0		4.5	V
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS} = \pm 20\text{V}_{DC}, V_{DS} = 0\text{ V}, T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$			± 100 ± 200	nA
Drain-to-Source Leakage Current (Zero Gate Voltage Drain Current)	I_{DSS}	$V_{DS} = 0.8 \cdot BV_{DSS}, T_J = 25^\circ\text{C}$ $V_{GS} = 0\text{ V}, T_J = 125^\circ\text{C}$			200 1000	μA
Static Drain-to-Source On-State Resistance (1)	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 5\text{ A}, T_J = 25^\circ\text{C}$ $I_D = 10\text{ A}, T_J = 25^\circ\text{C}$ $I_D = 5\text{ A}, T_J = 125^\circ\text{C}$		1.1 2	1.1	Ω
Forward Transconductance (1)	g_{fs}	$V_{DS} \geq 10\text{ V}; I_D = 5\text{ A}$	6	12		S
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		4200		μF
Output Capacitance	C_{oss}			315		
Reverse Transfer Capacitance	C_{rss}			90		
Turn-on Delay Time	$T_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 450\text{ V},$ $I_D = 5\text{ A}, R_G = 2.00\ \Omega$		20	50	ns
Rise Time	t_r			15	50	
Turn-off Delay Time	$t_{d(off)}$			50	100	
Fall Time	t_f			20	50	
Total Gate Charge	$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 450\text{ V}, I_D = 5\text{ A}$		125	155	nC
Gate-to-Source Charge	Q_{gs}			30	45	
Gate-to-Drain (Miller) Charge	Q_{gd}			50	80	
Body Diode Forward Voltage (1)	V_{SD}	$I_F = I_S, V_{GS} = 0\text{ V}$			1.5	V
Reverse Recovery Time (Body Diode)	t_{rr}	$I_F = 10\text{ A},$ 25 C $-di/dt = 100\text{ A}/\mu\text{s},$ 125 C			250 400	ns
Reverse Recovery Charge	Q_{rr}	$I_F = 10\text{ A},$ 25 C $di/dt = 100\text{ A}/\mu\text{s},$ 125 C		1 2		μC

Notes

- (1) Pulse test, $t \leq 300\text{ ms}$, duty cycle $\leq 2\%$
- (2) Microsemi Corp. does not manufacture the mosfet die; contact company for details.